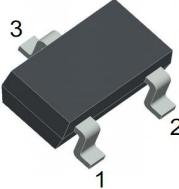
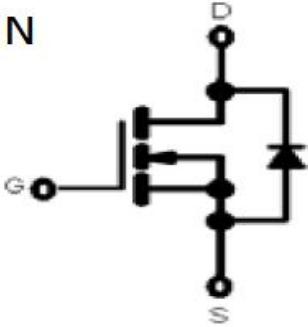
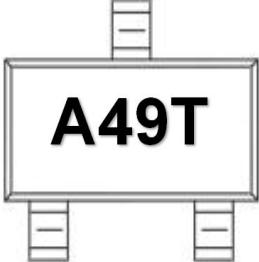


N-Channel 30-V(D-S) MOSFET	SOT-23 Plastic-Encapsulate MOSFETS			
<p><u>SOT-23</u></p>  <p>1.GATE 2.SOURCE 3.DRAIN</p> <p><b>Equivalent Circuit:</b></p> 	<p><b>DESCRIPTION :</b></p> <p>The AO3404 use advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.</p> <p><b>MARKING:</b></p> 			
V(BR)DSS	RDS(on)MAX			
30 V	<table border="1"> <tr> <td>24.5mΩ@10V</td> <td rowspan="2">5.8A</td> </tr> <tr> <td>37mΩ@4.5V</td> </tr> </table>	24.5mΩ@10V	5.8A	37mΩ@4.5V
24.5mΩ@10V	5.8A			
37mΩ@4.5V				
<b>Mosfet Maximum ratings ( Ta=25°C unless otherwise noted)</b>				
Parameter	Symbol	Value	Unit	
Drain-Source Voltage	VDS	30	V	
Gate-Source Voltage	VGS	±20		
Continuous Drain Current	ID	5.8	A	
Pulsed drain current *	IDM	30		
Power Dissipation	PD	1.0	W	
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	200	°C/W	
Junction Temperature	T <sub>J</sub>	150	°C	
Storage Temperature	T <sub>STG</sub>	-55~+150	°C	

\* Repetitive rating : Pulse width limited by maximum junction temperature.

### MOSFET ELECTRICAL CHARACTERISTICS

unless otherwise specified  $T_a = 25^\circ C$

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Parameters</b>						
Drain-source breakdown voltage	$V(BR)_{DSS}$	$V_{GS} = 0V, ID = 250\mu A$	30			V
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, ID = 250\mu A$	1		2.5	V
Gate-body leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 16V$			$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$			1	$\mu A$
Drain-source on-resistancea	$R_{DS(on)}$	$V_{GS} = 10V, ID = 1A$		18	24.5	$m\Omega$
		$V_{GS} = 4.5V, ID = 1A$		27	37	$m\Omega$
Forward transconductancea	$g_{fs}$	$V_{DS} = 10V, ID = 1A$	5			S
Diode forward voltage	$V_{SD}$	$I_S = 1A, V_{GS} = 0V$		0.8	1.28	V
<b>Dynamic Parameters</b>						
Input capacitance	$C_{iss}$	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$			820	pF
Output capacitance	$C_{oss}$			118		pF
Reverse transfer capacitanceb	$C_{rss}$			85		pF
Gate resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$			1.5	$\Omega$
<b>Switching Parameters</b>						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 15V, RL = 2.6\Omega, R_{GEN} = 3\Omega$		4.5	6.5	ns
Rise time	$t_r$			3.1		ns
Turn-off delay time	$t_{d(off)}$			15.1		ns
Fall time	$t_f$			2.7		ns

#### Note :

- These parameters have no way to verify.
- Pulse Test ; Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 0.5\%$